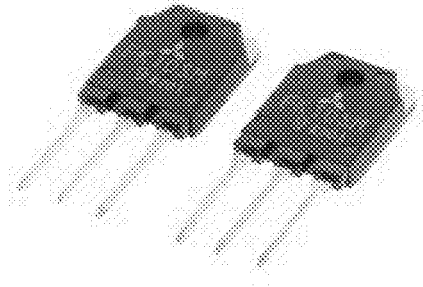


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HIGH-SPEED SWITCHING USE

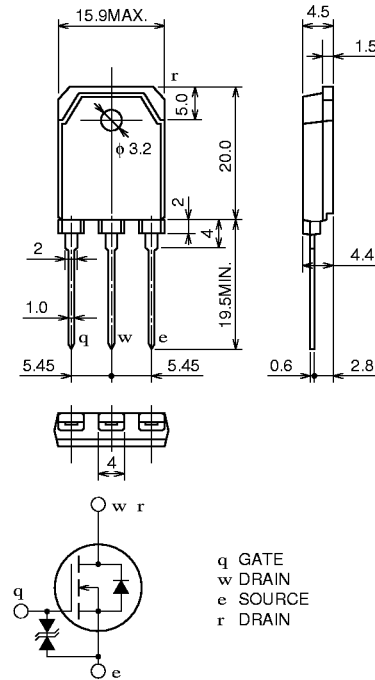
FK10SM-9



- ˘ V_{DSS}450V
- ˘ r_{DS (ON)} (MAX) 0.92Ω
- ˘ I_D 10A
- ˘ Integrated Fast Recovery Diode (MAX.) 150ns

OUTLINE DRAWING

Dimensions in mm



TO-3P

APPLICATION

Servo motor drive, Robot, UPS, Inverter Fluorescent lamp, etc.

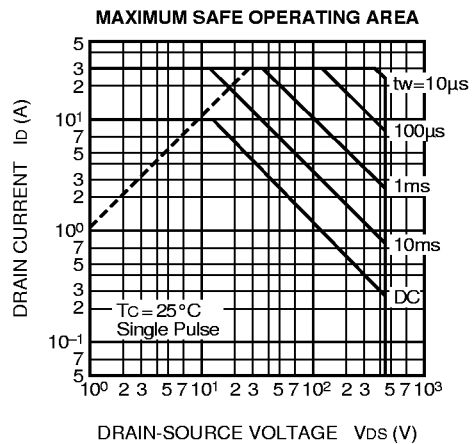
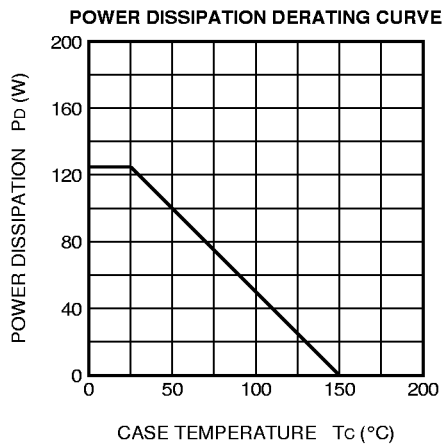
MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	450	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±30	V
I _D	Drain current		10	A
I _{DM}	Drain current (Pulsed)		30	A
I _S	Source current		10	A
I _{SM}	Source current (Pulsed)		30	A
P _D	Maximum power dissipation		125	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	4.8	g

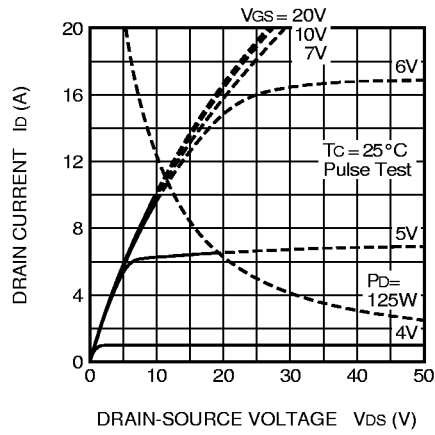
ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR) DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 V	450	—	—	V
V _{(BR) GSS}	Gate-source breakdown voltage	I _G = ±100 μA, V _{DS} = 0 V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25 V, V _{DS} = 0 V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 450 V, V _{GS} = 0 V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1 mA, V _{DS} = 10 V	2	3	4	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 5 A, V _{GS} = 10 V	—	0.70	0.92	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 5 A, V _{GS} = 10 V	—	3.50	4.60	V
y _{fs}	Forward transfer admittance	I _D = 5 A, V _{DS} = 10 V	3.3	5.5	—	S
C _{iss}	Input capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	—	1100	—	pF
C _{oss}	Output capacitance		—	130	—	pF
C _{rss}	Reverse transfer capacitance		—	20	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200 V, I _D = 5 A, V _{GS} = 10 V, R _{GEN} = R _{GS} = 50 Ω	—	20	—	ns
t _r	Rise time		—	30	—	ns
t _d (off)	Turn-off delay time		—	95	—	ns
t _f	Fall time		—	35	—	ns
V _{SD}	Source-drain voltage	I _S = 5 A, V _{GS} = 0 V	—	1.5	2.0	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	1.00	°C/W
t _{rr}	Reverse recovery time	I _S = 10 A, di/dt = -100 A/μs	—	—	150	ns

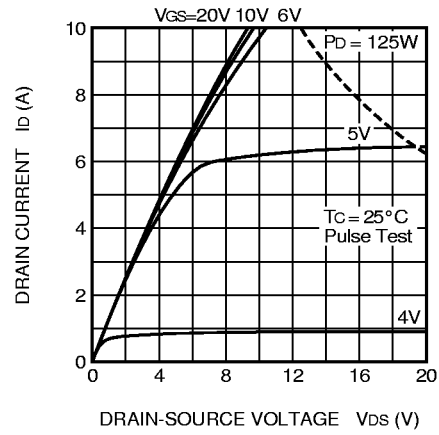
PERFORMANCE CURVES



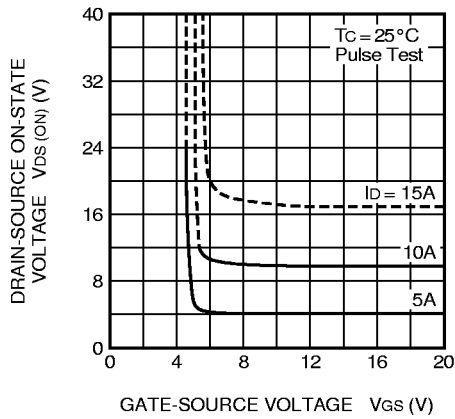
OUTPUT CHARACTERISTICS
(TYPICAL)



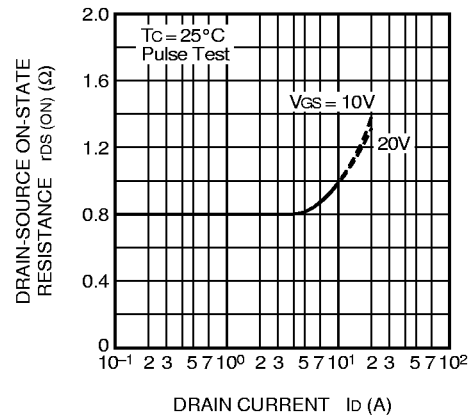
OUTPUT CHARACTERISTICS
(TYPICAL)



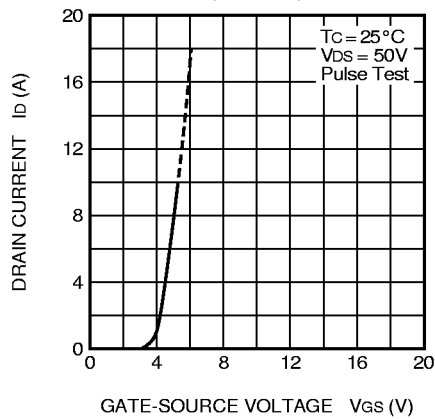
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



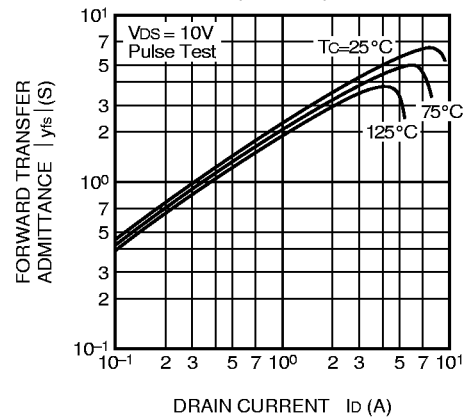
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)

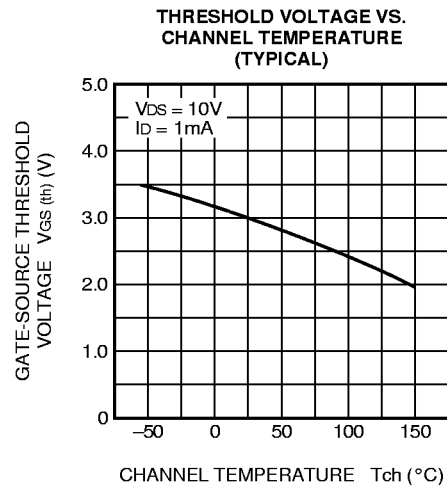
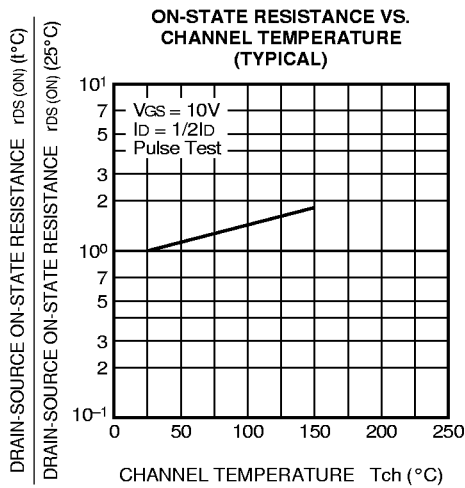
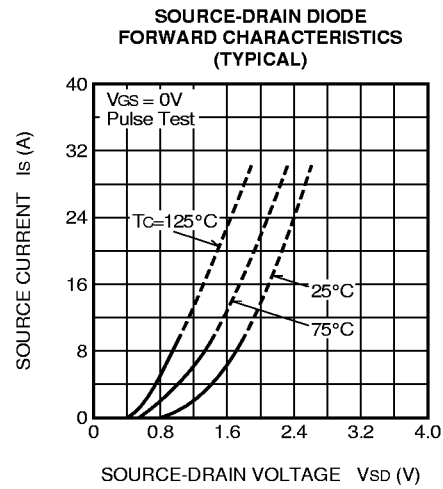
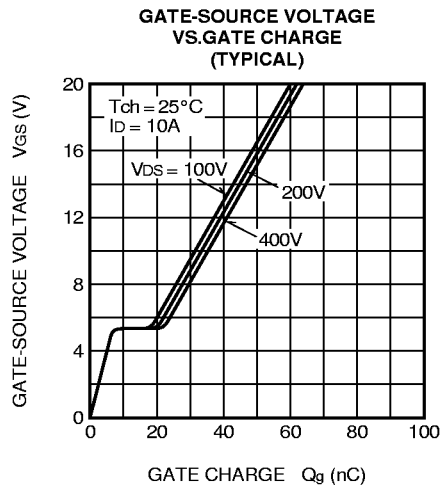
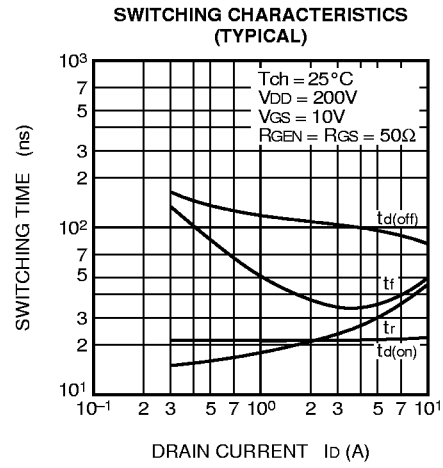
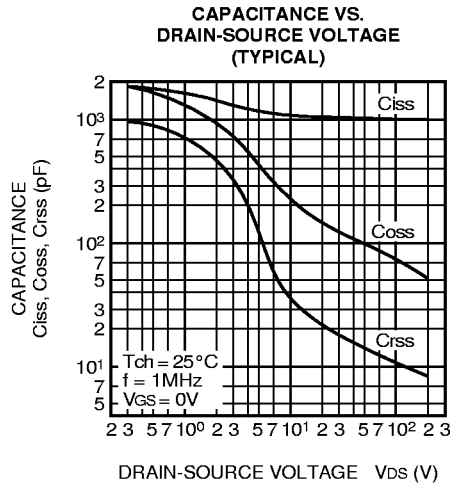


TRANSFER CHARACTERISTICS
(TYPICAL)



FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)





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HIGH-SPEED SWITCHING USE

